Supporting Information (SI)

Tailoring the structural and electronic properties of SnSe$_2$/MoS$_2$ van der Waals heterostructure by electric field and the insertion of graphene sheet

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Fig. S1. Band structures of (a) MoS$_2$, (b) SnSe$_2$, and (c) SnSe$_2$/MoS$_2$ vdWH given by HSE06 method.

Fig. S2. Projected band structure of the SnSe$_2$/G/MoS$_2$ vdWH given by HSE06 method.

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